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Apr 23, 1999

PUB-NO: JP411111845A

DOCUMENT-IDENTIFIER: JP 11111845 A

TITLE: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

PUBN-DATE: April 23, 1999

## INVENTOR-INFORMATION:

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APPL-NO: JP09271134

APPL-DATE: October 3, 1997

INT-CL (IPC): H01L 21/768; H01L 21/316; H01L 21/318

## ABSTRACT:

PROBLEM TO BE SOLVED: To provide a semiconductor device which can suppress impurity diffusion and infiltration of water or hydroxyl ions for improving its reliability.

SOLUTION: Formed on an element isolation insulating film 11 is a wiring layer 20 of a plurality of first metal wiring lines. Formed on the insulating film 11 and the first metallic wiring layer 20 are a silicon oxide film 31 added in high concentration of fluorine, a silicon nitride film 32 and an SiO<sub>2</sub> film 33. The SiO<sub>2</sub> film 33 higher in relative permittivity than the SiOF film 31 but lower than that of the silicon nitride film 32. Formed, in the SiOF film 31, silicon nitride film 32 and SiO<sub>2</sub> film 33 is a via hole for connection with the first wiring layer 20. A W plug material 41 is embedded in the via hole. A second metal wiring layer 50 is formed on the SiO<sub>2</sub> film 33.

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